

# BCR08DS-14A

700V-0.8A-Triac

R07DS0258EJ0300

Rev.3.00

Low Power Use

Dec 01, 2014

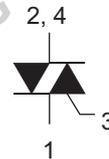
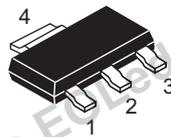
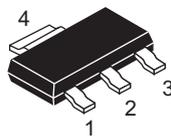
## Features

- $I_{T(RMS)}$  : 0.8 A
- $V_{DRM}$  : 700 V
- $I_{FGT}$ ,  $I_{RGT}$ ,  $I_{RGTIII}$  : 5 mA
- Planar Passivation Type
- Surface Mounted Type
- Completed Pb Free

## Outline

RENESAS Package code: PRSP0004ZB-A  
(Package name: SOT-223)

RENESAS Package code: PRSP0004ZA-A  
(Package name: SOT-223)



1. T<sub>1</sub> Terminal
2. T<sub>2</sub> Terminal
3. Gate Terminal
4. T<sub>2</sub> Terminal

## Applications

Washing machine, electric fan, air cleaner, other general purpose control applications

## Maximum Ratings

| Parameter   | Symbol    | Voltage class | Unit |
|---|-----------|---------------|------|
|   |           | 14            |      |
| Repetitive peak off-state voltage <sup>Note1</sup>      | $V_{DRM}$ | 700           | V    |
| Non- repetitive peak off-state voltage <sup>Note1</sup> | $V_{DSM}$ | 840           | V    |

Notes: 1. Gate open.

| Parameter                      | Symbol       | Ratings      | Unit             | Conditions  |
|--------------------------------|--------------|--------------|------------------|---|
| RMS on-state current           | $I_{T(RMS)}$ | 0.8          | A                | Commercial frequency, sine full wave 360° conduction, $T_c = 96^\circ\text{C}$ <sup>Note3</sup> |
| Surge on-state current         | $I_{TSM}$    | 8            | A                | 60Hz sinewave 1 full cycle, peak value, non-repetitive  |
| $I^2t$ for fusing              | $I^2t$       | 0.26         | A <sup>2</sup> s | Value corresponding to 1 cycle of half wave 60Hz, surge on-state current                        |
| Peak gate power dissipation    | $P_{GM}$     | 1            | W                |   |
| Average gate power dissipation | $P_{G(AV)}$  | 0.1          | W                |   |
| Peak gate voltage              | $V_{GM}$     | 6            | V                |   |
| Peak gate current              | $I_{GM}$     | 0.5          | A                |   |
| Junction temperature           | $T_j$        | - 40 to +125 | °C               |   |
| Storage temperature            | $T_{stg}$    | - 40 to +125 | °C               |   |
| Mass                           | —            | 0.12         | g                | Typical value   |

## Electrical Characteristics

| Parameter   | Symbol        | BCR08DS-14A#B10<br>BCR08DS-14A#BD0 |      |      | BCR08DS-14A#B11 |      |      | Unit               | Test conditions  |   |
|---|---------------|------------------------------------|------|------|-----------------|------|------|--------------------|--|---|
|   |               | Min.                               | Typ. | Max. | Min.            | Typ. | Max. |                    |  |   |
| Repetitive peak off-state current                                       | $I_{DRM}$     | —                                  | —    | 1.0  | —               | —    | 1.0  | mA                 | $T_j = 125^\circ\text{C}$<br>$V_{DRM}$ applied                           |   |
| On-state voltage  | $V_{TM}$      | —                                  | —    | 2.0  | —               | —    | 2.0  | V                  | $T_c = 25^\circ\text{C}$ , $I_{TM} = 1.2$ A<br>instantaneous measurement |   |
| Gate trigger voltage <sup>Note2</sup>                                   | I             | $V_{FGTI}$                         | —    | —    | 2.0             | —    | —    | 2.0                | V  | $T_j = 25^\circ\text{C}$ , $V_D = 6$ V<br>$R_L = 6 \Omega$ , $R_G = 330 \Omega$ |
|   | II            | $V_{RGTI}$                         | —    | —    | 2.0             | —    | —    | 2.0                | V  |   |
|   | III           | $V_{RGTIII}$                       | —    | —    | 2.0             | —    | —    | 2.0                | V  |   |
|   | IV            | $V_{FGTIII}$                       | —    | —    | —               | —    | —    | 2.0                | V  |   |
| Gate trigger current <sup>Note2</sup>                                   | I             | $I_{FGTI}$                         | —    | —    | 5               | —    | —    | 5                  | mA   | $T_j = 25^\circ\text{C}$ , $V_D = 6$ V<br>$R_L = 6 \Omega$ , $R_G = 330 \Omega$ |
|   | II            | $I_{RGTI}$                         | —    | —    | 5               | —    | —    | 5                  | mA   |   |
|   | III           | $I_{RGTIII}$                       | —    | —    | 5               | —    | —    | 5                  | mA   |   |
|   | IV            | $I_{FGTIII}$                       | —    | —    | —               | —    | —    | 7                  | mA   |   |
| Gate non-trigger voltage  | $V_{GD}$      | 0.2                                | —    | —    | 0.2             | —    | —    | V                  | $T_j = 125^\circ\text{C}$<br>$V_D = 1/2 V_{DRM}$                         |   |
| Thermal resistance  | $R_{th(j-c)}$ | —                                  | —    | 25   | —               | —    | 25   | $^\circ\text{C/W}$ | Junction to case <sup>Note3</sup>  |   |
| Critical-rate of rise of off-state commutating voltage <sup>Note4</sup> | $(dv/dt)_c$   | 0.5                                | —    | —    | 0.5             | —    | —    | V/ $\mu\text{s}$   | $T_j = 125^\circ\text{C}$  |   |
| Critical-rate of rise of off-state voltage <sup>Note5</sup>             | $dv/dt$       | 200                                | —    | —    | 200             | —    | —    | V/ $\mu\text{s}$   | $T_j = 125^\circ\text{C}$  |   |

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured on the  $T_2$  tab.

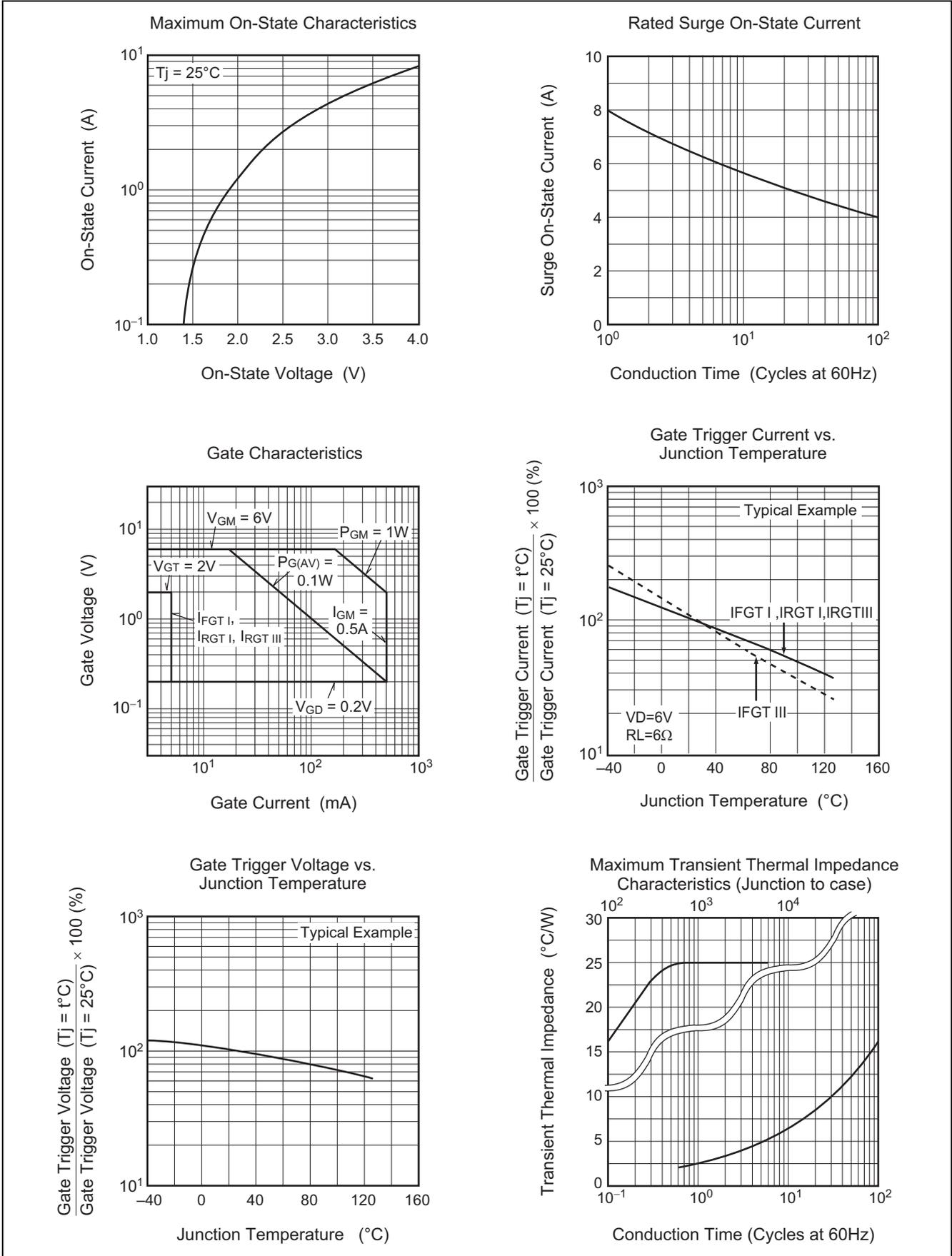
4. Test conditions of the critical-rate of rise of off-state commutating voltage are shown in the table below.

| Test conditions   | Commutating voltage and current waveforms (inductive load) |
|---|--|
| 1. Junction temperature<br>$T_j = 125^\circ\text{C}$<br>2. Rate of decay of on-state commutating current<br>$(di/dt)_c = -0.4$ A/ms<br>3. Peak off-state voltage<br>$V_D = 400$ V |  |

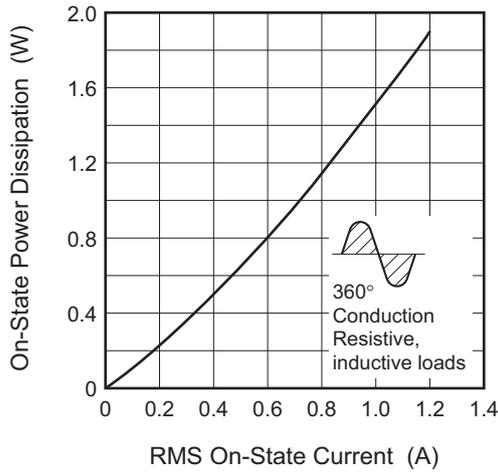
5. Test conditions of the critical-rate of rise of off-state voltage are shown in the table below.

| Test conditions  | Off-state voltage waveforms |
|--|-----------------------------|
| 1. Junction temperature<br>$T_j = 125^\circ\text{C}$<br>2. Off-state voltage waveform<br>Linear waveform<br>3. Peak off-state voltage<br>$V_D = 200$ V<br>4. Gate open |                             |

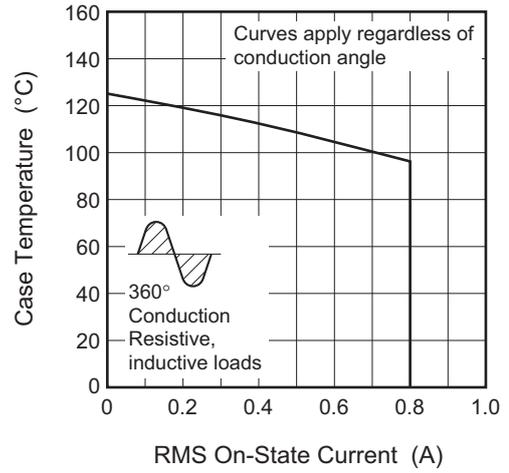
Performance Curves



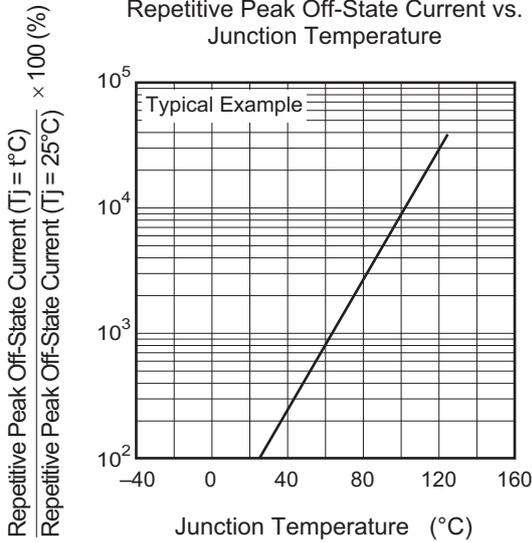
Maximum On-State Power Dissipation



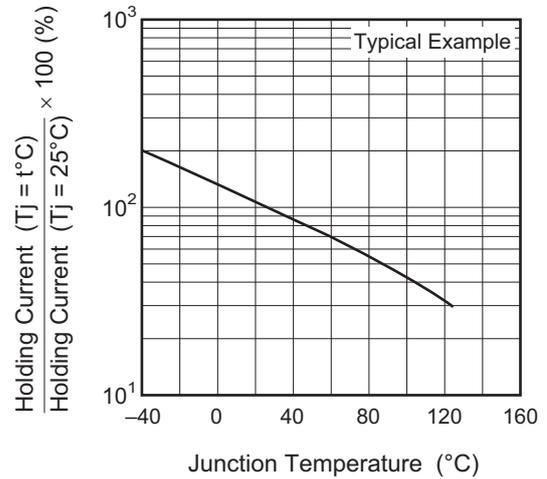
Allowable Case Temperature vs. RMS On-State Current



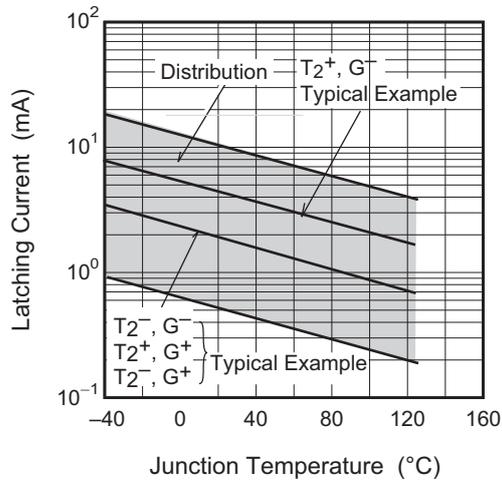
Repetitive Peak Off-State Current vs. Junction Temperature



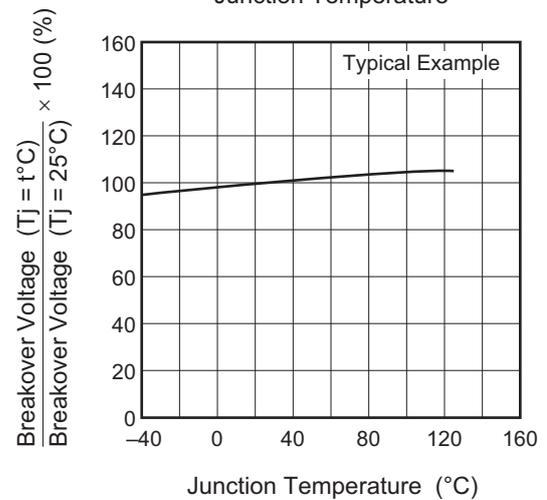
Holding Current vs. Junction Temperature



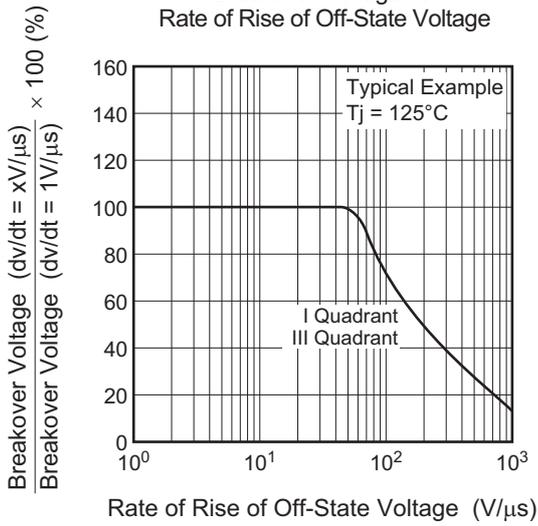
Latching Current vs. Junction Temperature



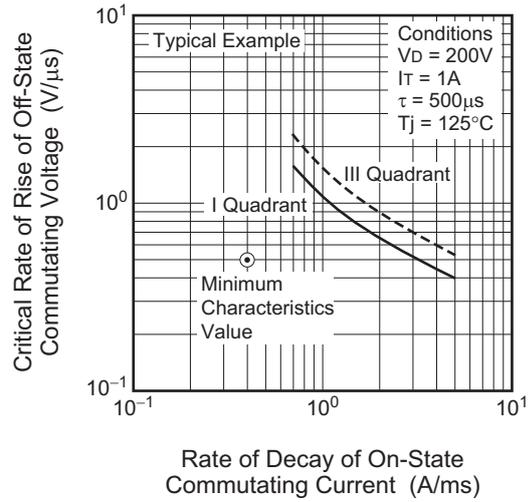
Breakover Voltage vs. Junction Temperature



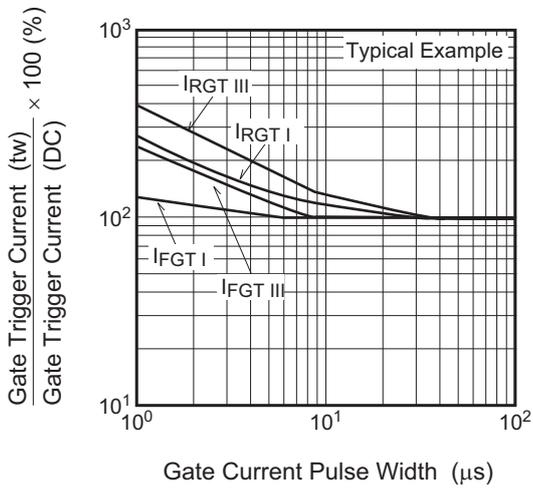
Breakover Voltage vs. Rate of Rise of Off-State Voltage



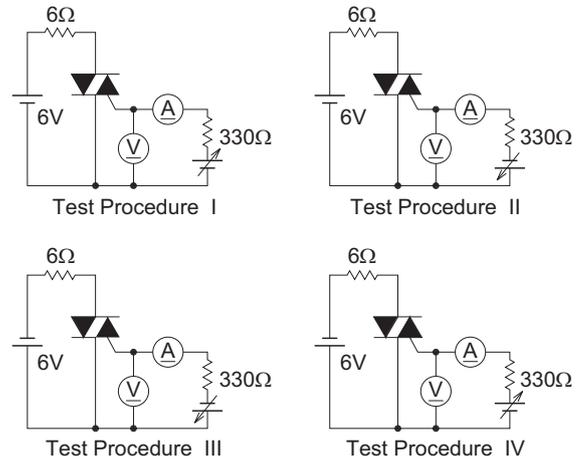
Commutation Characteristics (Tj=125°C)



Gate Trigger Current vs. Gate Current Pulse Width



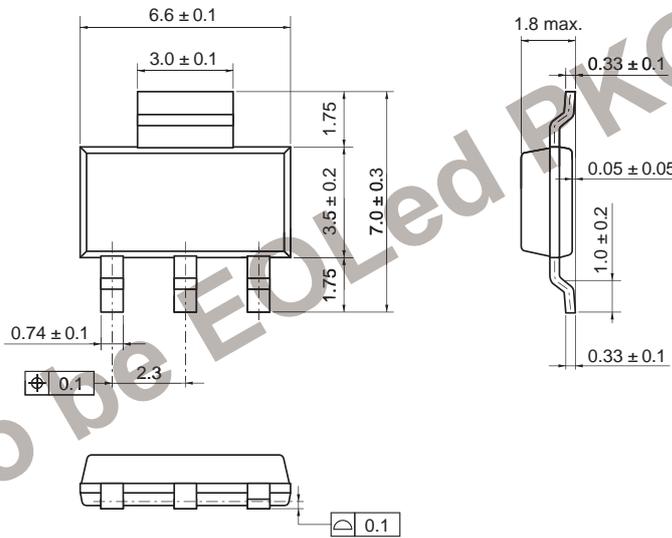
Gate Trigger Characteristics Test Circuits



### Package Dimensions

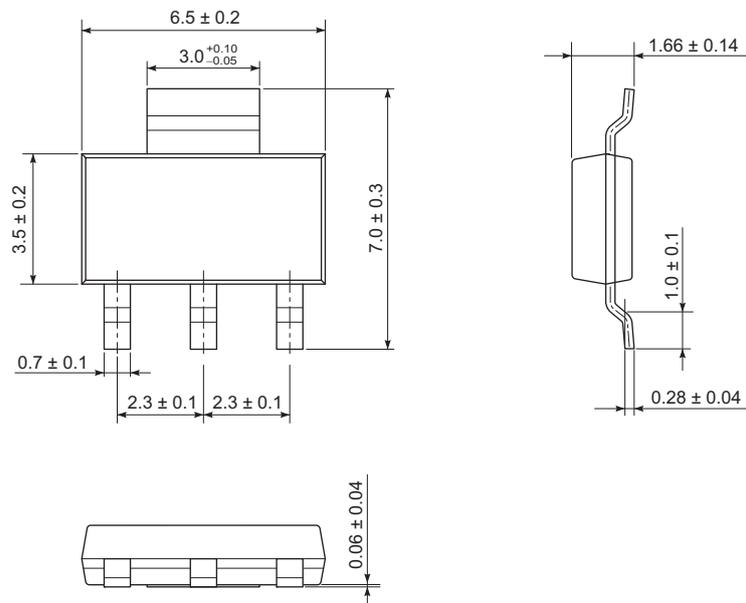
| Package Name | JEITA Package Code | RENESAS Code | Previous Code | MASS[Typ.] |
|--------------|--------------------|--------------|---------------|------------|
| SOT-223      | —                  | PRSP0004ZA-A | —             | 0.12g      |

Unit: mm



| Package Name | JEITA Package Code | RENESAS Code | Previous Code | MASS[Typ.] |
|--------------|--------------------|--------------|---------------|------------|
| SOT-223      | —                  | PRSP0004ZB-A | SOT-223A      | 0.12g      |

Unit: mm



**Ordering Information**

| <b>Orderable Part Number</b> | <b>Packing</b> | <b>Quantity</b> | <b>Remark</b>                  |
|------------------------------|----------------|-----------------|--------------------------------|
| BCR08DS-14AT13#B10           | Embossed Tape  | 3000 pcs.       | Not Recommended for New Design |
| BCR08DS-14AT13#B11           | Embossed Tape  | 3000 pcs.       | Not Recommended for New Design |
| BCR08DS-14AT13#BD0           | Embossed Tape  | 3000 pcs.       | Taping direction "T1"          |

Note : Please confirm the specification about the shipping in detail.

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